BUK763R8-80E

N-channel TrenchMOS standard level FET

Rev. 2 — 16 May 2012 Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

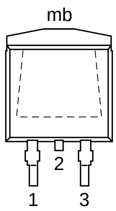
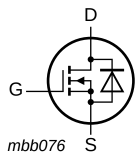
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	80	V
I_D	drain current	$V_{GS} = 10$ V; $T_{mb} = 25$ °C; see Figure 1	[1]	-	-	120	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2		-	-	357	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10$ V; $I_D = 25$ A; $T_j = 25$ °C; see Figure 11		-	3.1	3.8	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 10$ V; $I_D = 25$ A; $V_{DS} = 64$ V; see Figure 13; see Figure 14		-	51	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SOT404 (D2PAK)	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK763R8-80E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes

Type number	Marking code
BUK763R8-80E	BUK763R8-80E

5. Limiting values

Table 5. Limiting values

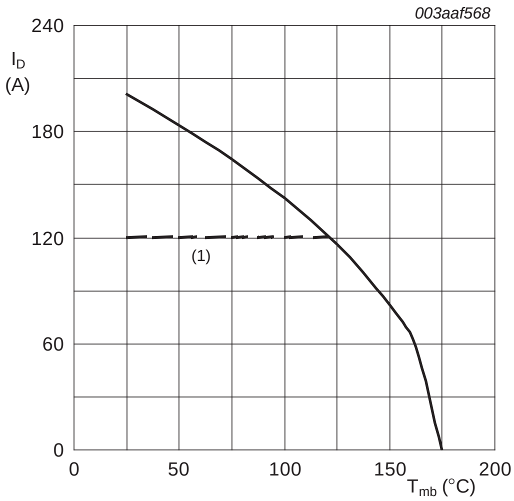
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	80	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20$ kΩ		-	80	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; see Figure 1	[1]	-	120	A
		$T_{mb} = 100$ °C; $V_{GS} = 10$ V; see Figure 1	[1]	-	120	A
I_{DM}	peak drain current	$T_{mb} = 25$ °C; pulsed; $t_p \leq 10$ µs; see Figure 4		-	786	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; see Figure 2		-	357	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25$ °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C		-	786	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 120$ A; $V_{sup} \leq 80$ V; $R_{GS} = 50$ Ω; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; unclamped; see Figure 3	[2][3]	-	488	mJ

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

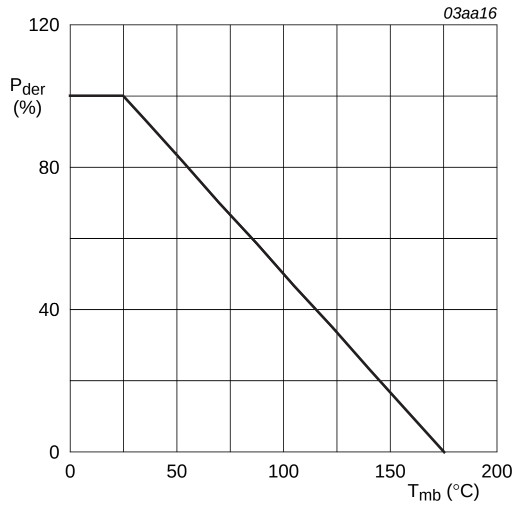
[3] Refer to application note AN10273 for further information.



$V_{GS} \geq 10\,V$

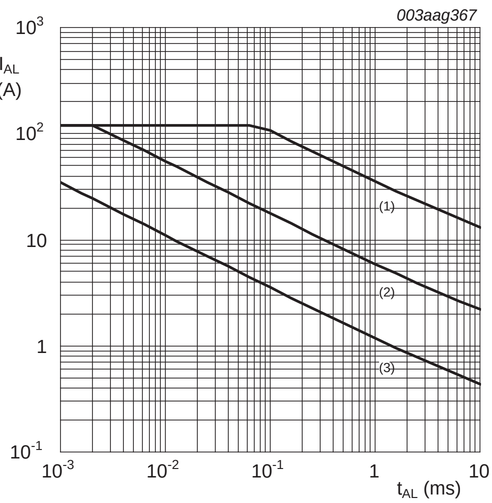
(1) Capped at 120 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j\,(init)} = 25\,^{\circ}C$; (2) $T_{j\,(init)} = 150\,^{\circ}C$; (3) Repetitive Avalanche

Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time

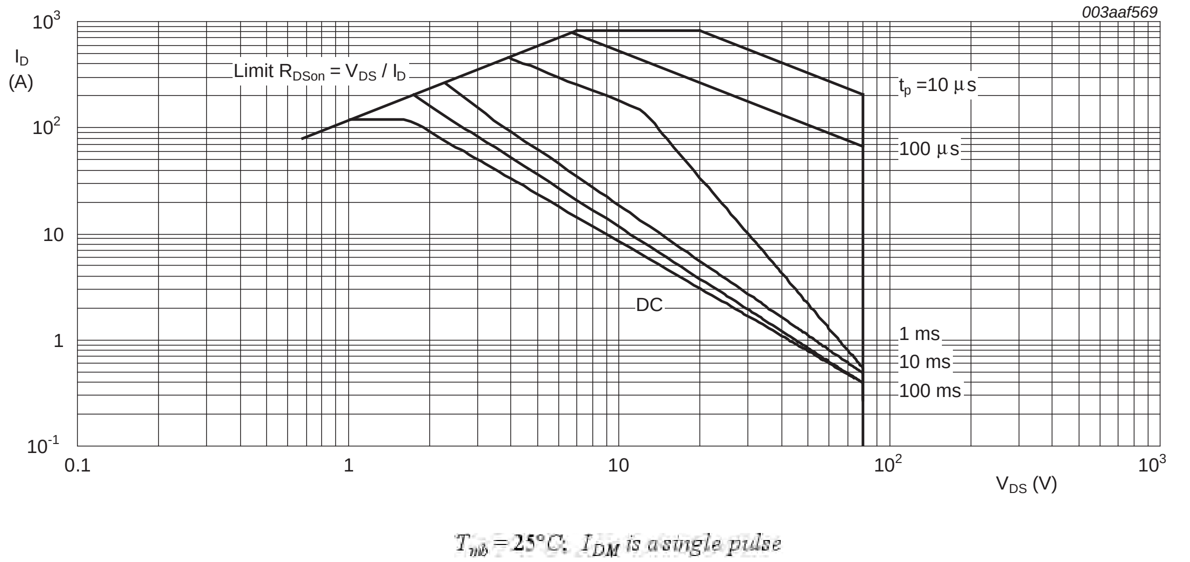


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	0.42	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

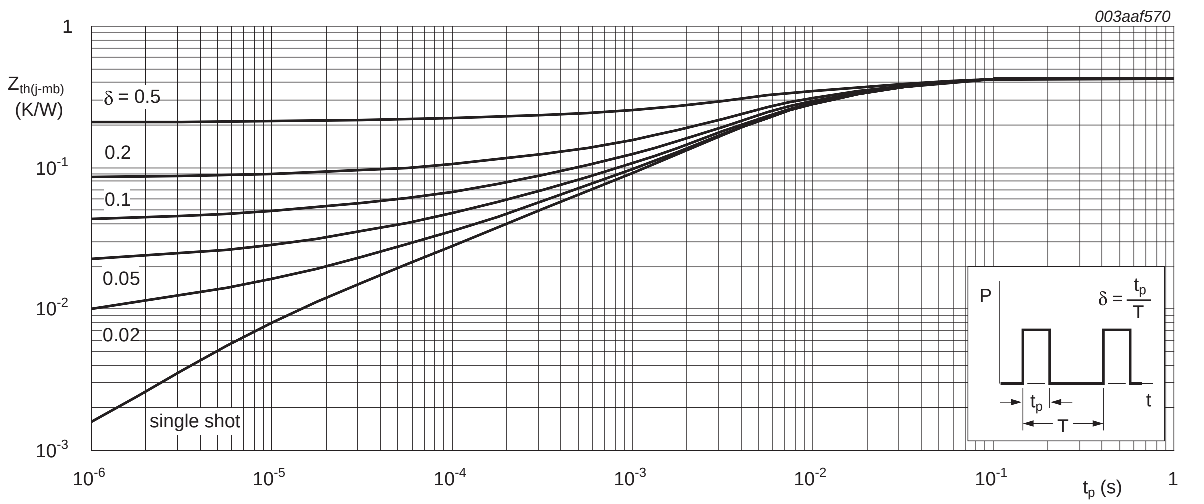
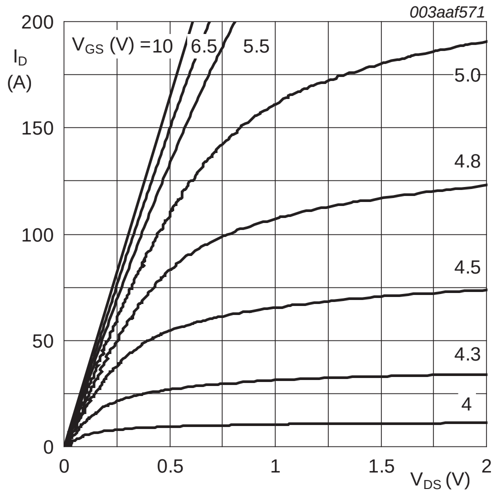


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

7. Characteristics

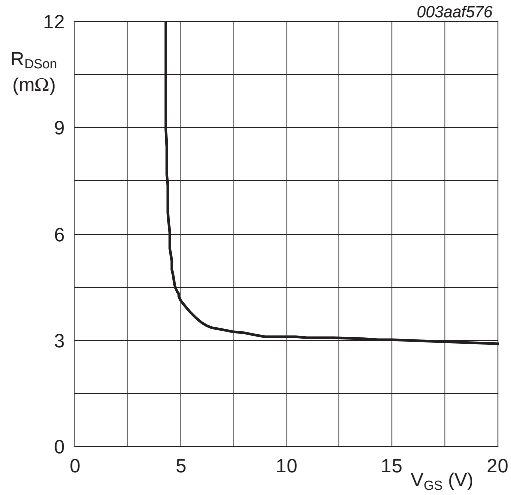
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
		I_D = 250 mA; V_{GS} = 0 V; T_j = -55 °C	72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 9; see Figure 10	2.4	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 9	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 9	-	-	4.5	V
I_{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.15	2	µA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 11	-	3.1	3.8	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 12; see Figure 11	-	-	9.2	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 64 V; V_{GS} = 10 V; see Figure 13; see Figure 14	-	169	-	nC
Q_{GS}	gate-source charge		-	37	-	nC
Q_{GD}	gate-drain charge		-	51	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; see Figure 15	-	9020	12030	pF
C_{oss}	output capacitance		-	840	1010	pF
C_{rss}	reverse transfer capacitance		-	470	645	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 60 V; R_L = 2.4 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω	-	38	-	ns
t_r	rise time		-	48	-	ns
$t_{d(off)}$	turn-off delay time		-	129	-	ns
t_f	fall time		-	65	-	ns
L_D	internal drain inductance	from upper edge of mounting base to centre of die	-	2.5	-	nH
L_S	internal source inductance	measured from source lead to source bond pad; T_j = 25 °C	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 16	-	0.77	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V	-	58	-	ns
Q_r	recovered charge		-	121	-	nC



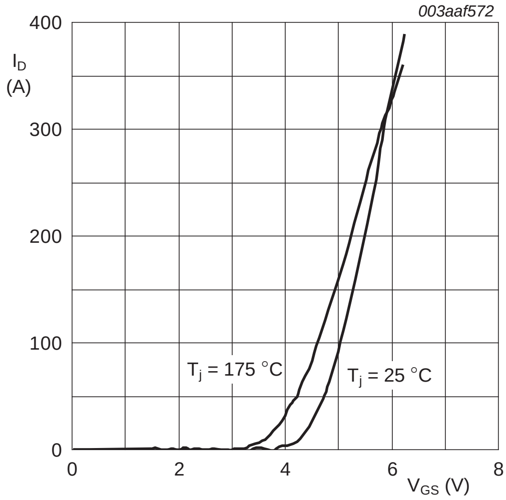
T_j = 25 °C; t_p = 300 μs

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



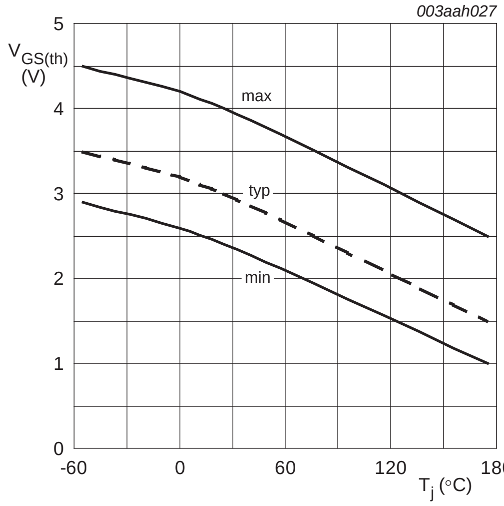
$T_j = 25\,°C; I_D = 25A$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



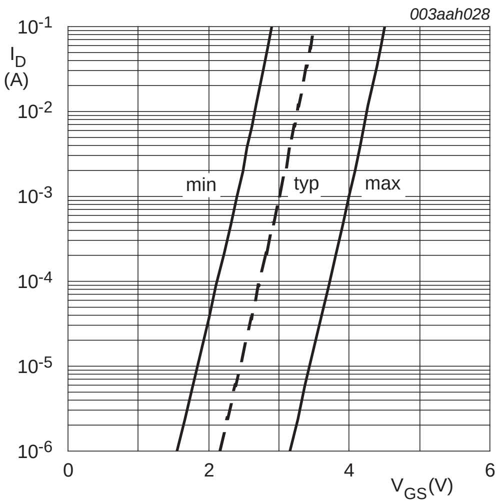
$V_{DS} = 12\,V$

Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



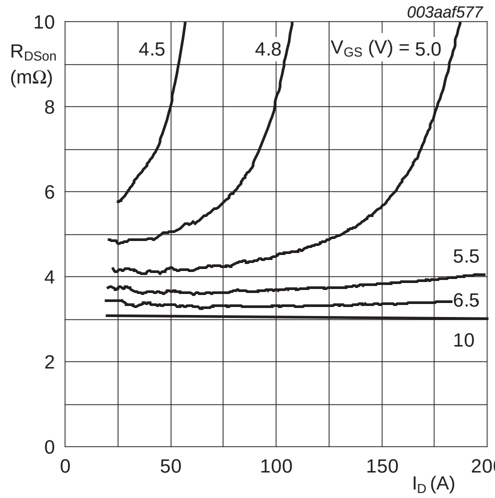
$I_D = 1$ mA; $V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature



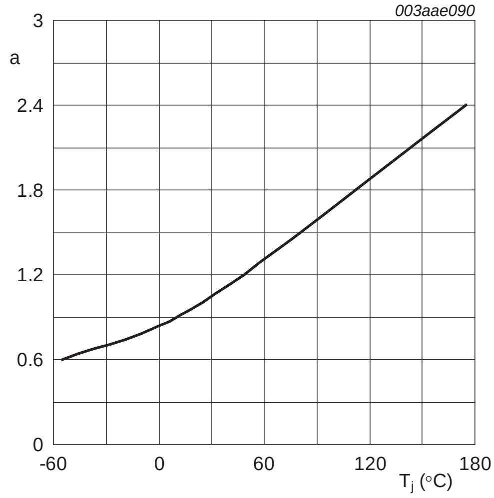
$T_j = 25°C;\ V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



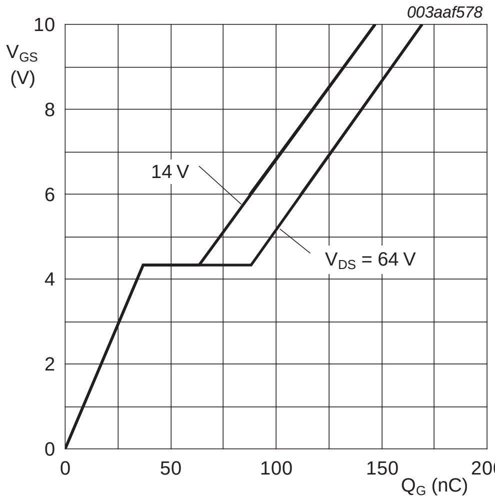
T_j = 25 °C; t_p = 300 µs

Fig 11. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



T_j = 25 °C; I_D = 25 A

Fig 13. Gate-source voltage as a function of gate charge; typical values

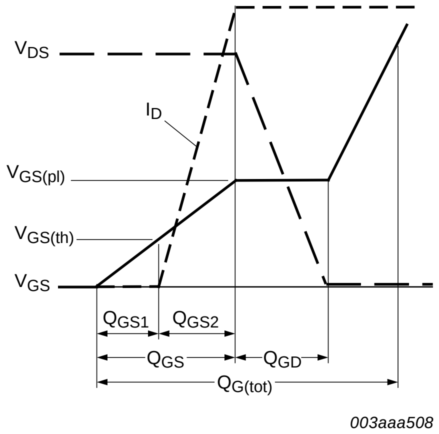
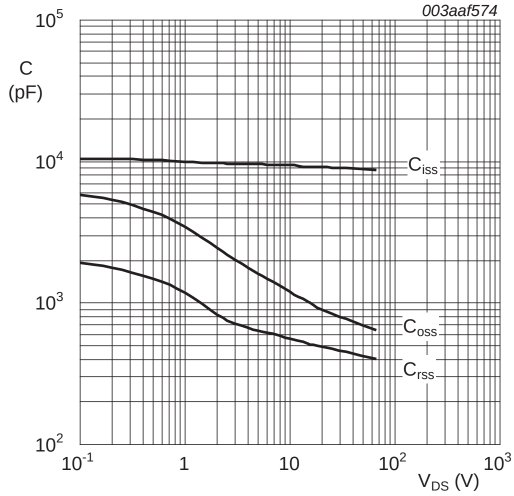
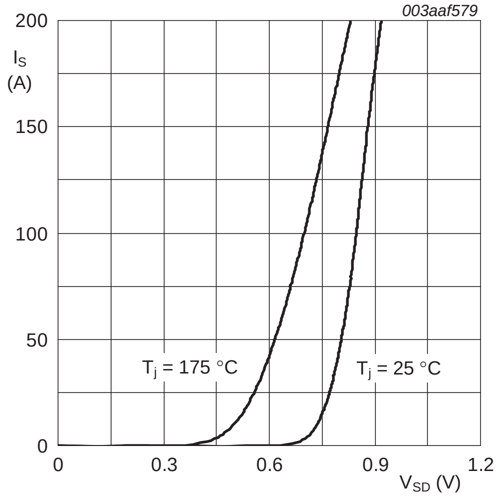


Fig 14. Gate charge waveform definitions



V_{GS} = 0 V; f = 1 MHz

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

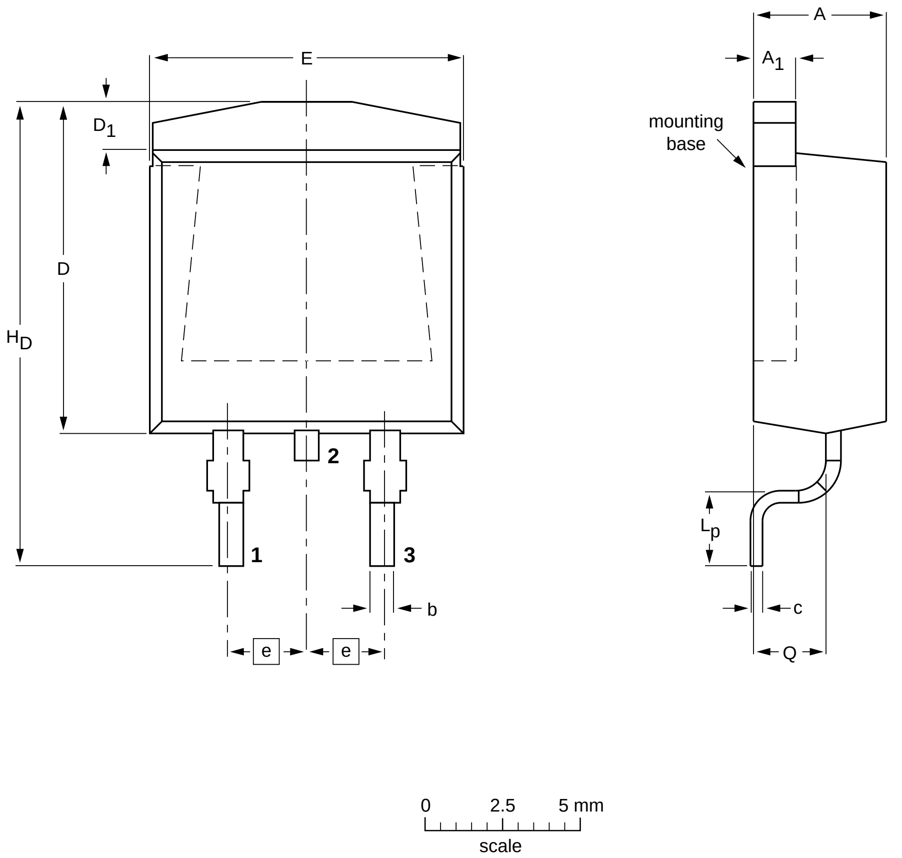


V_{GS} = 0 V

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

8. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) **SOT404**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D max.	D_1	E	e	L_p	H_D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						~~05-02-11~~ 06-03-16

Fig 17. Package outline SOT404 (D2PAK)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK763R8-80E v.2	20120516	Product data sheet	-	BUK763R8-80E v.1
Modifications:	• Status changed from objective to product. • Various changes to content.			
BUK763R8-80E v.1	20120404	Objective data sheet	-	-

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10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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12. Contents

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